IWPH01-02
Si PIN PHOTODIODE

Visible to infrared range
Plastic package 7 mm x 7.8 mm
Active area size 2.8 mm x 2.8 mm

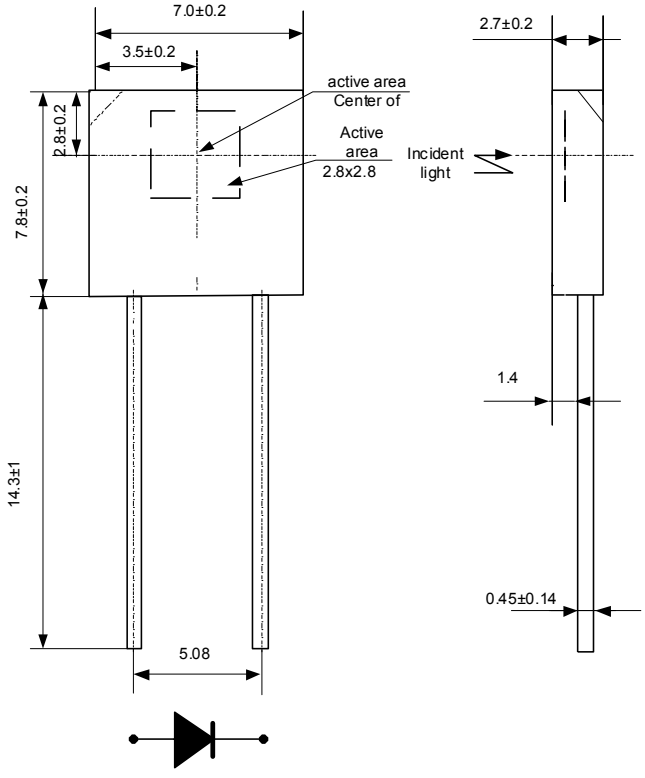
Absolute maximum ratings

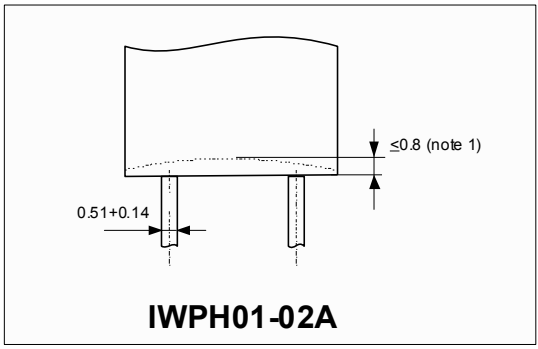
	Parameter	Max.	Units
$V_{R\ max}$	Reverse voltage	35	V
P_{max}	Power dissipation	150	mW
T_{opr}	Operating temperature	-25 to +85	°C
T_{stg}	Storage temperature	-40 to +100	

Electrical and optical characteristics (Ta=25 ºC, unless otherwise noted)

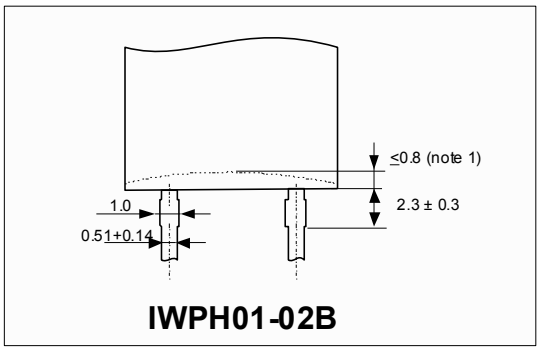
	Parameter	Typ	Max	Units	Conditions
λ	Spectral response range	320 to 1100		nm	
λ_p	Peak sensitivity wavelength	960			
S	Photo sensitivity	0.57		A/W	960 nm
		0.38			660 nm
		0.46			780 nm
		0.48			830 nm
I_{sc}	Short circuit current	7.5		μA	100 *lx*
I_D	Dark current	0.1	10	nA	V_R=12V
T_{CID}	Temp. coefficient of I_D	1.15		times/°C	
	NEP	$1.0x10^{-14}$		$W/Hz^{1/2}$	V_R=12V

Package outline (unit: mm, tolerance unless otherwise noted: ±0.1)





IWPH01-02A



IWPH01-02B

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BELMICROSYSTEMS

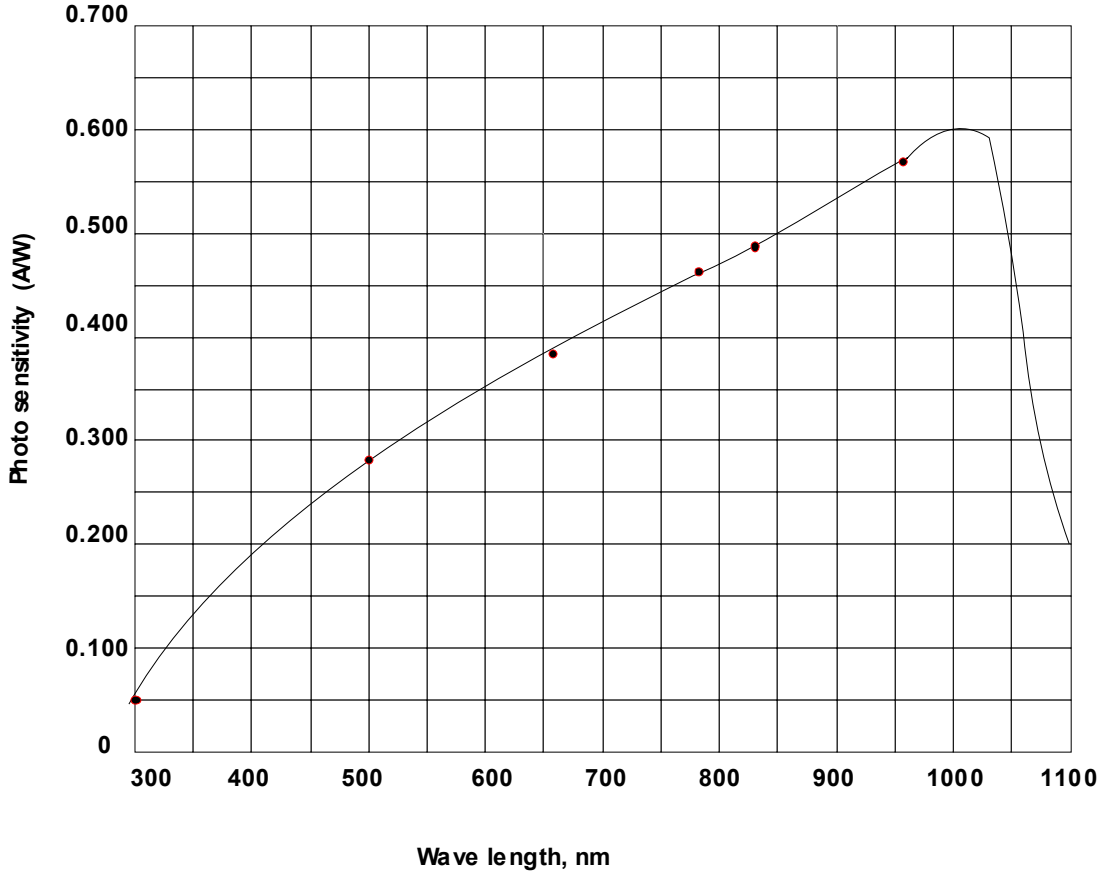
Note 1 Shape of surface at zone (≤0.8) not defined

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IWPH01-02

Spectral response

(Typ. Ta=25°C)



- **Directivity**

